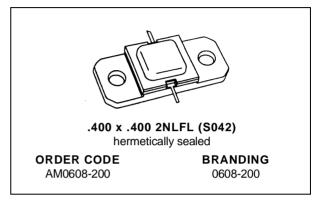


AM0608-200

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

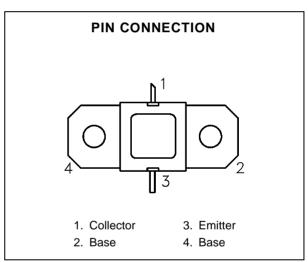
PRELIMINARY DATA

- REFRACTORY/GOLD METALLIZATION
- INTERNAL INPUT MATCHING
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 220 W MIN. WITH 8.7 dB GAIN



DESCRIPTION

The AM0608-200 is an internally-matched, common base silicon bipolar device optimized pulsed application in the 600 - 750 MHz frequency range. Housed in the industry-standard AMPAC™ metal/ceramic package, this device uses a refractory/gold overlay die geometry for ruggedness and long-term reliability.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

	(55.55 /			
Symbol	Parameter	Value	Unit	
P _{DISS}	Power Dissipation* $(T_C \le 75^{\circ}C)$	875	W	
Ic	Device Current*	16.0	А	
Vcc	Collector-Supply Voltage*	55	V	
TJ	Junction Temperature (Pulsed RF Operation)	ature (Pulsed RF Operation) 250		
T _{STG}	Storage Temperature	- 65 to +200	°C	

THERMAL DATA

_			0
R _{TH(j-c)}	Junction-Case Thermal Resistance*	0.20	°C/W

^{*}Applies only to rated RF amplifier operation

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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

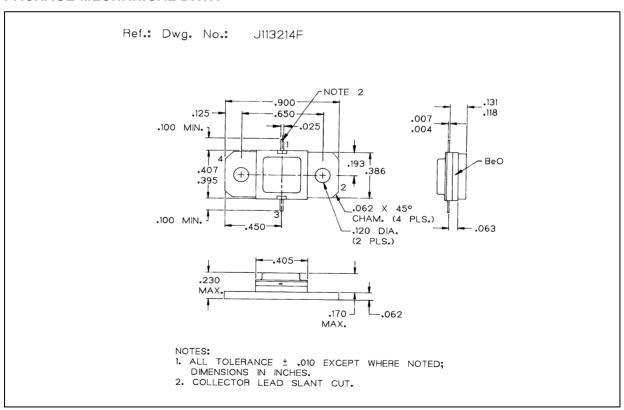
			Value			
Symbol		Test Conditions	Min.	Тур.	Max.	Unit
ВУсво	$I_C = 10mA$	$I_E = 0mA$	65	_	_	V
BV _{EBO}	I _E = 1mA	I _C = 0mA	3.5	_	_	V
BVcer	IC = 25mA	$R_{BE} = 10\Omega$	65	_	_	V
ICES	$V_{BE} = 0V$	$V_{CE} = 50V$		_	25	mA
h_{FE}	$V_{CE} = 5V$	$I_C = 1mA$	15	_	120	_

DYNAMIC

				Value			
Symbol		Test Conditions		Min.	Тур.	Max.	Unit
Pout	f = 600 — 750MHz	$P_{IN}=30W$	$V_{CC} = 50V$	220	_	_	W
ης	f = 600 — 750MHz	$P_{IN} = 30W$	$V_{CC} = 50V$	40		_	%
G _P	f = 600 — 750MHz	$P_{IN} = 30W$	$V_{CC} = 50V$	8.7	_	_	dB

Note: Pulse Width = $10\mu Sec$ Duty Cycle = 1%

PACKAGE MECHANICAL DATA



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